

L Number	Hits	Search Text	DB	Time stamp
1	2539	((438/585) or (438/769) or (438/770) or (438/775) or (438/763) or (438/766) or (438/914)).CCLS.	USPAT; US-PGPUB	2004/03/24 10:42
2	18	(implant\$ with (nitrogen "N.sub.2")) and (different adj thickness)	EPO; JPO; DERWENT; IBM_TDB	2004/03/24 10:48
3	11	438/FOR.272.ccls.	EPO; JPO; DERWENT; IBM_TDB	2004/03/24 10:48
-	315	(implant\$ with (nitrogen "N.sub.2")) with (gate adj (insulat\$ or oxide))	USPAT; US-PGPUB	2004/03/18 19:17
-	171	((implant\$ with (nitrogen "N.sub.2")) with (gate adj (insulat\$ or oxide))) and (oxidiz\$)	USPAT; US-PGPUB	2004/03/18 19:16
-	34	((implant\$ with (nitrogen "N.sub.2")) with (gate adj (insulat\$ or oxide))) and ((oxidiz\$) with implant\$)	USPAT; US-PGPUB	2004/03/18 19:16
-	9	(implant\$ with (nitrogen "N.sub.2")) with (oxidat\$ oxidiz\$) with (different near2 thickness)	USPAT; US-PGPUB	2004/03/18 19:20
-	2	(implant\$ with (nitrogen "N.sub.2")) same (oxidat\$ oxidiz\$ oxide) same (different near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/23 14:12
-	5412	(implant\$ with (nitrogen "N.sub.2")) same2 (different near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/18 19:26
-	3	(implant\$ with (nitrogen "N.sub.2")) same (different near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/23 14:13
-	0	(implant\$ with (nitrogen "N.sub.2")) same ((various varied vary varies) near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/18 19:24
-	3	(implant\$ with (nitrogen "N.sub.2")) same (different near2 thick\$) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/18 19:25
-	2584	((implant\$ with (nitrogen "N.sub.2")) same2 (different near2 thickness) same (sidewall spacer)) and (oxidiz\$ oxidat\$)	USPAT; US-PGPUB	2004/03/18 19:25
-	3669	(implant\$ with (nitrogen "N.sub.2")) same2 ((different near2 thickness) same (sidewall spacer) same (oxidat\$ oxidiz\$))	USPAT; US-PGPUB	2004/03/18 19:27
-	3633	(implant\$ with (nitrogen "N.sub.2")) same2 ((different near2 thickness) with (sidewall spacer) with (oxidat\$ oxidiz\$))	USPAT; US-PGPUB	2004/03/18 19:28
-	3627	(implant\$ with (nitrogen "N.sub.2")) same2 ((different near2 thickness) with (sidewall spacer) with (oxidat\$ oxidiz\$) with (implant\$))	USPAT; US-PGPUB	2004/03/18 19:30
-	17	(implant\$ with (nitrogen "N.sub.2")) with (different adj thickness) with (gate transistor)	USPAT; US-PGPUB	2004/03/24 10:44
-	13	(implant\$ with (nitrogen "N.sub.2")) with (thick\$) with (sidewall)	USPAT; US-PGPUB	2004/03/18 20:12
-	1	("5872376").PN.	USPAT; US-PGPUB	2004/03/18 19:47
-	21	(implant\$ with (nitrogen "N.sub.2")) with (thick\$) with (top perpendicular normal)	USPAT; US-PGPUB	2004/03/18 20:34

-	1	("6531362").PN.	USPAT; US-PGPUB	2004/03/18 20:34
-	2	((dop\$ implant\$) with (nitrogen "N.sub.2")) same (oxidat\$ oxidiz\$ oxide) same (different near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/23 14:12
-	3	((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/23 14:13
-	61	((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness)	USPAT; US-PGPUB	2004/03/23 14:18
-	594	((dop\$ implant\$) with (different near2 thickness))	USPAT; US-PGPUB	2004/03/23 14:18
-	61	((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness\$)	USPAT; US-PGPUB	2004/03/23 14:19
-	594	((dop\$ implant\$) with (different near2 thickness\$))	USPAT; US-PGPUB	2004/03/23 15:40
-	553	((dop\$ implant\$) with (different near2 thickness\$)) not ((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness\$))	USPAT; US-PGPUB	2004/03/23 14:19
-	204	((dop\$ implant\$) with (different near2 thickness\$)) not ((dop\$ implant\$) with (nitrogen "N.sub.2")) same (different near2 thickness\$)) and (sidewall or spacer)	USPAT; US-PGPUB	2004/03/23 15:22
-	6969	(oxidizing oxidize oxide oxidation oxidized) same (gate transistor fet mosfet) same (thicker thick thinner thickness thicknesses) same (sidewall spacer)	USPAT; US-PGPUB	2004/03/23 15:49
-	42	(different near2 thickness\$) with (oxide oxidation oxidize oxidized oxidizing) with (spacer sidewall)	USPAT; US-PGPUB	2004/03/23 15:41
-	3975	(oxidizing oxidize oxide oxidation oxidized) same (gate transistor fet mosfet) same (thicker thick thinner thickness thicknesses) same (sidewall spacer) same (dop\$ implant\$ inject\$)	USPAT; US-PGPUB	2004/03/23 15:50
-	434	((thick thickness thicknesses thicker thinner) with (spacer sidewall) with (substrate)) same (oxidizing oxide oxidation oxidize oxidized) same (dop\$ implant\$ inject\$)	USPAT; US-PGPUB	2004/03/23 17:56
-	4	(vertical near2 implant\$) same (sidewall or spacer) same (thicker thicknesses thickness thinner thick) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	USPAT; US-PGPUB	2004/03/23 16:01
-	17	(vertical\$ near2 (dop\$ implant\$)) same (sidewall or spacer) same (thicker thicknesses thickness thinner thick) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	USPAT; US-PGPUB	2004/03/23 16:11
-	4	(vertical\$ near2 (dop\$ implant\$)) same ((sidewall or spacer) with (thicker thicknesses thickness thinner thick)) same (oxidation oxidize oxidizing reoxidation oxidized reoxidized)	USPAT; US-PGPUB	2004/03/23 16:14
-	20	(vertical\$ near2 (dop\$ implant\$)) same ((sidewall or spacer) with (thicker thicknesses thickness thinner thick))and(oxidation oxidize oxidizing reoxidation oxidized reoxidized)	USPAT; US-PGPUB	2004/03/23 16:14

-	556	((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxide oxidation oxidize oxidized)).ab.	USPAT; US-PGPUB	2004/03/23 17:57
-	385	((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxide oxidation oxidize oxidized) and (gate fet mosfet transistor)).ab.	USPAT; US-PGPUB	2004/03/23 17:58
-	198	((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxide oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 17:59
-	43	((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 18:09
-	33	((thick thickness thicknesses thicker thinner) and (sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 18:10
-	53	((thick thickness thicknesses thicker thinner thin) and (sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 18:14
-	20	((thick thickness thicknesses thicker thinner thin) and (sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.) not ((thick thickness thicknesses thicker thinner) and (spacer sidewall) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.)	USPAT; US-PGPUB	2004/03/23 18:11
-	299	((thick thickness thicknesses thicker thinner thin) and (gate mosfet transistor fet) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 18:15
-	16	((differ differing different) near3 thickness) and (gate mosfet transistor fet) and (oxidizing oxidation oxidize oxidized) and (gate fet mosfet transistor) and (implant\$ or dop\$ or inject\$)).ab.	USPAT; US-PGPUB	2004/03/23 18:25
-	1	("5648287").PN.	USPAT; US-PGPUB	2004/03/23 18:26
-	26020	((("5648287").PN.) and kev or ev	USPAT; US-PGPUB	2004/03/23 18:26
-	1	((("5648287").PN.) and (kev or ev)	USPAT; US-PGPUB	2004/03/23 18:26